

# **PSMN017-30BL**

# N-channel 30 V 17 m $\Omega$ logic level MOSFET in D2PAK Rev. 2 — 3 April 2012 Product

**Product data sheet** 

#### 1. **Product profile**

## 1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
$I_D$	drain current	$T_{mb} = 25  ^{\circ}\text{C}; V_{GS} = 10  \text{V}; \text{see } \frac{\text{Figure 1}}{}$	1 -	-	32	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	47	W
Tj	junction temperature		-55	-	175	°C
Static char	acteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	18.6	23.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	13.3	17	mΩ
Dynamic c	haracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 15 \text{ V};$	-	1.94	-	nC
Q <sub>G(tot)</sub>	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.1	-	nC
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 32 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	-	13	mJ

<sup>[1]</sup> Continuous current is limited by package.



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN017-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

Table 4. Limiting values

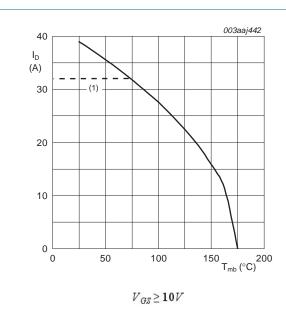
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	25.5	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	[1]	-	32	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3		-	154	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	47	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	32	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	154	Α
Avalanche ru	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 32 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	13	mJ

<sup>[1]</sup> Continuous current is limited by package.

PSMN017-30BL

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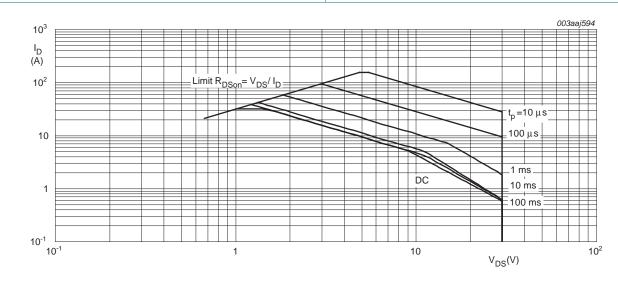


(1) Capped at 32A due to package

120 80 40 0 150 T<sub>mb</sub> (°C)  $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$ 

Fig 1. Continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



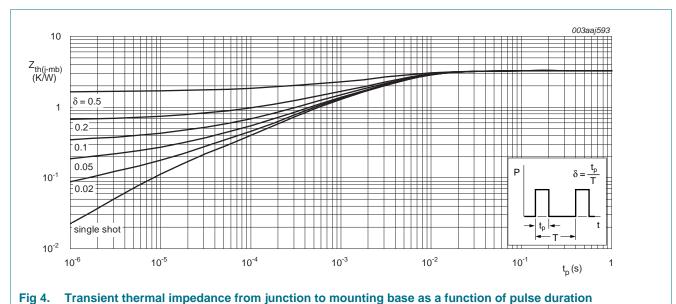
 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	3.18	3.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	50	-	K/W



## 6. Characteristics

Table 6. Characteristics

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	- - 2.15 - 2.45 1 50 100 100 43 23.3	V V V V PA
$\begin{array}{c} V_{(BR)DSS} & drain-source breakdown \\ voltage & \\ \hline \\ V_{D} = 250~\mu A;~V_{GS} = 0~V;~T_{j} = 25~^{\circ}C \\ 27 & - & - \\ \hline \\ I_{D} = 250~\mu A;~V_{GS} = 0~V;~T_{j} = -55~^{\circ}C \\ 27 & - & - \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = 25~^{\circ}C; \\ see Figure 10; see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = 25~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ I_{D} = 1~mA;~V_{DS} = V_{GS};~T_{j} = -55~^{\circ}C; \\ see Figure 11 \\ \hline \\ V_{DS} = 30~V;~V_{SS} = 0~V;~T_{j} = 25~^{\circ}C \\ \hline \\ V_{DS} = 30~V;~V_{DS} = 0~V;~T_{j} = 25~^{\circ}C \\ \hline \\ V_{DS} = 30~V;~V_{DS} = 0~V;~T_{j} = 25~^{\circ}C \\ \hline \\ V_{GS} = 16~V;~V_{DS} = 0~V;~T_{j} = 25~^{\circ}C \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 0~V;~T_{j} = 25~^{\circ}C \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~A;~T_{j} = 175~^{\circ}C; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~A;~T_{j} = 175~^{\circ}C; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~A;~T_{j} = 10~^{\circ}C; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~A;~T_{j} = 25~^{\circ}C; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~A;~T_{j} = 25~^{\circ}C; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~A;~T_{j} = 25~^{\circ}C; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~V;~V_{DS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~V;~V_{DS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{DS} = 10~V;~V_{CS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10~V; \\ \hline \\ V_{GS} = 10~V;~V_{GS} = 10~V;~V_{GS} = 10$	- 2.15 - 2.45 1 50 100 100 43 23.3 31.5	V V V V μΑ μΑ nA nA mΩ
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	- 2.15 - 2.45 1 50 100 100 43 23.3 31.5	V V V V μΑ μΑ nA nA mΩ
$V_{GS(th)}  \text{gate-source threshold voltage}  \begin{array}{l} I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 25  ^{\circ}\text{C}; \\ \text{see Figure 10; see Figure 11} \\ I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 11} \\ I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 11} \\ I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 11} \\ I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 11} \\ I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 11} \\ I_D = 1 \text{ mA; } V_{DS} = V_{GS;} T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{DSS}  \text{drain leakage current}  V_{DS} = 30  V;  V_{GS} = 0  V;  T_j = 25  ^{\circ}\text{C} \\ \text{see Figure 12} \\ I_{GSS}  \text{gate leakage current}  V_{GS} = 16  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ}\text{C} \\ \text{see Figure 12} \\ I_{GS} = 16  V;  V_{DS} = 0  V;  T_j = 25  ^{\circ}\text{C} \\ \text{see Figure 12} \\ I_{GS} = 4.5  V;  I_D = 10  A;  T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 4.5  V;  I_D = 10  A;  T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 10  V;  I_D = 10  A;  T_j = 175  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 10  V;  I_D = 10  A;  T_j = 100  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 10  V;  I_D = 10  A;  T_j = 100  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 10  V;  I_D = 10  A;  T_j = 100  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 10  V;  I_D = 10  A;  T_j = 100  ^{\circ}\text{C}; \\ \text{see Figure 12} \\ I_{GS} = 10  V;  I_D = 10  A;  T_J = 25  ^{\circ}\text{C}; \\ \text{see Figure 13} \\ I_{D} = 0  A;  V_{DS} = 15  V;  V_{GS} = 10  V; \\ \text{see Figure 15} \\ I_{D} = 0  A;  V_{DS} = 0  V;  V_{GS} = 10  V; \\ \text{see Figure 15} \\ I_{D} = 10  A;  V_{DS} = 15  V;  V_{GS} = 10  V; \\ \text{see Figure 15} \\ I_{D} = 10  A;  V_{DS} = 15  V;  V_{GS} = 4.5  V; \\ \text{see Figure 15} \\ I_{D} = 10  A;  V_{DS} = 15  V;  V_{GS} = 4.5  V; \\ \text{see Figure 15} \\ I_{D} = 10  A;  V_{DS} = 15  V;  V_{GS} = 4.5  V; \\ \text{see Figure 15} \\ I_{D} = 10  A;  V_{DS} = 15  V;  V_{GS} = 4.5  V; \\$	2.15 - 2.45 1 50 100 100 43 23.3 31.5	V V V μΑ μΑ nA mΩ mΩ
	- 2.45 1 50 100 100 43 23.3 31.5	V V μΑ μΑ nA nA mΩ
	2.45 1 50 100 100 43 23.3 31.5	V μΑ μΑ nA mΩ mΩ
	1 50 100 100 43 23.3 31.5	μΑ μΑ nA nA mΩ mΩ
$V_{DS} = 30 \text{ V; } V_{GS} = 0 \text{ V; } T_j = 125 \text{ °C} \qquad - \qquad $	50 100 100 43 23.3 31.5	μΑ nA nA mΩ mΩ
$ \begin{array}{c} I_{GSS} \qquad \text{gate leakage current} \qquad V_{GS} = 16 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C} \qquad - \qquad 10 $	100 100 43 23.3 31.5	nA nA mΩ mΩ
$V_{GS} = -16 \text{ V; } V_{DS} = 0 \text{ V; } T_j = 25 \text{ °C} \qquad - \qquad 10 $	100 43 23.3 31.5	nA mΩ mΩ
$ \begin{array}{c} R_{DSon} & drain-source \ on\text{-state} \\ resistance & \begin{array}{c} V_{GS} = 4.5 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \hline \\ v_{GS} = 4.5 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \hline \\ see \ \frac{Figure \ 12}{Figure \ 13} \\ \hline \\ V_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 175 \ ^{\circ}\text{C}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 100 \ ^{\circ}\text{C}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 100 \ ^{\circ}\text{C}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ T_j = 25 \ ^{\circ}\text{C}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ V_{DS} = 15 \ \text{V}; \ V_{GS} = 10 \ \text{V}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ V_{DS} = 15 \ \text{V}; \ V_{GS} = 10 \ \text{V}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text{A}; \ l_D = 10 \ \text{A}; \\ \hline \\ v_{GS} = 10 \ \text{V}; \ l_D = 10 \ \text$	43 23.3 31.5	$m\Omega$ $m\Omega$
	23.3 31.5	mΩ mΩ
	31.5	mΩ
	23.5	$m\Omega$
$\begin{array}{c} \textbf{Dynamic characteristics} \\ \textbf{Q}_{G(tot)} & \text{total gate charge} & \textbf{I}_{D} = 10 \text{ A; V}_{DS} = 15 \text{ V; V}_{GS} = 10 \text{ V;} & - & 10.7 & - \\ & & & & & & & & & & & & \\ \hline \textbf{I}_{D} = 0 \text{ A; V}_{DS} = 0 \text{ V; V}_{GS} = 10 \text{ V;} & - & 9.55 & - \\ & & & & & & & & & & \\ \hline \textbf{I}_{D} = 0 \text{ A; V}_{DS} = 0 \text{ V; V}_{GS} = 10 \text{ V;} & - & 9.55 & - \\ & & & & & & & & & \\ \hline \textbf{I}_{D} = 10 \text{ A; V}_{DS} = 15 \text{ V; V}_{GS} = 4.5 \text{ V;} & - & 5.1 & - \\ \hline \end{array}$	17	mΩ
$ \begin{array}{c} Q_{G(tot)} & \text{total gate charge} \\ & I_D = 10 \text{ A; } V_{DS} = 15 \text{ V; } V_{GS} = 10 \text{ V;} \\ & \text{see } \underline{\text{Figure 14; see }} \underline{\text{Figure 15}} \\ & I_D = 0 \text{ A; } V_{DS} = 0 \text{ V; } V_{GS} = 10 \text{ V;} \\ & \text{see } \underline{\text{Figure 14; see }} \underline{\text{Figure 15}} \\ & I_D = 10 \text{ A; } V_{DS} = 15 \text{ V; } V_{GS} = 4.5 \text{ V;} \end{array} $	-	Ω
see <u>Figure 14</u> ; see <u>Figure 15</u> $I_{D} = 0 \text{ A; } V_{DS} = 0 \text{ V; } V_{GS} = 10 \text{ V;} \qquad - \qquad 9.55 \qquad - \\ \text{see } \underline{\text{Figure 14}}; \text{ see } \underline{\text{Figure 15}} \\ I_{D} = 10 \text{ A; } V_{DS} = 15 \text{ V; } V_{GS} = 4.5 \text{ V;} \qquad - \qquad 5.1 \qquad - $		
see <u>Figure 14</u> ; see <u>Figure 15</u> $I_D = 10 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ - 5.1 -	-	nC
	-	nC
	-	nC
Q <sub>GS</sub> gate-source charge see <u>Figure 14</u> ; see <u>Figure 15</u> - 1.52 -	-	nC
Q <sub>GS(th)</sub> pre-threshold gate-source - 1 - charge	-	nC
Q <sub>GS(th-pl)</sub> post-threshold gate-source - 0.5 - charge	-	nC
Q <sub>GD</sub> gate-drain charge - 1.94 -	-	nC
$V_{GS(pl)}$ gate-source plateau voltage $I_D = 10 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; see Figure 14; - 2.86 - see Figure 15	-	V
-155	-	pF
$C_{oss}$ output capacitance $T_j = 25$ °C; see Figure 16 - 127 -	-	pF
C <sub>rss</sub> reverse transfer capacitance - 64 -		pF

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Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS}$ = 15 V; $R_{L}$ = 1.5 $\Omega$ ; $V_{GS}$ = 4.5 V; $R_{G(ext)}$ = 5 $\Omega$	-	10.7	-	ns
t <sub>r</sub>	rise time		-	9.2	-	ns
$t_{d(off)}$	turn-off delay time		-	11.4	-	ns
t <sub>f</sub>	fall time		-	5.1	-	ns
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	$I_S = 10 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 17</u>	-	0.89	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	17.3	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	6.5	-	nC

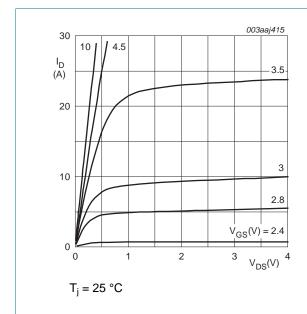


Fig 5. Output characteristics; drain current as a function of drain-source voltage; typical values

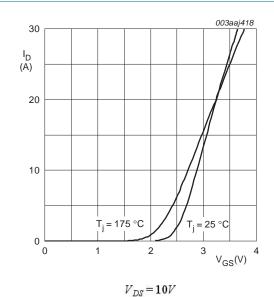


Fig 6. Transfer characteristics; drain current as a function of gate-source voltage; typical values

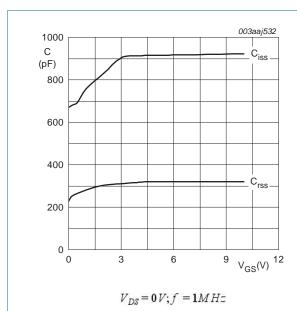


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

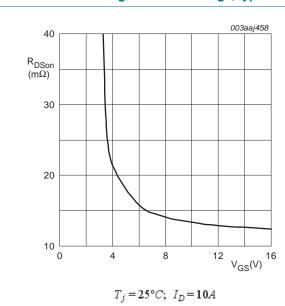


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

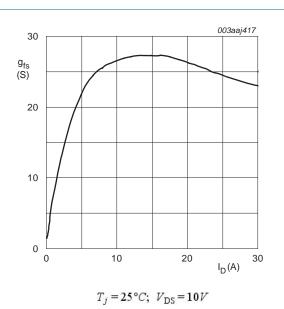
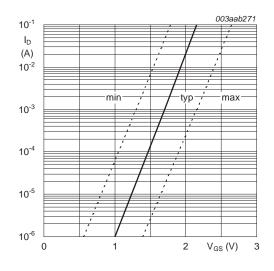


Fig 8. Forward transconductance as a function of drain current; typical values



 $T_j = 25\,^{\circ}C; V_{DS} = 5\,V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage

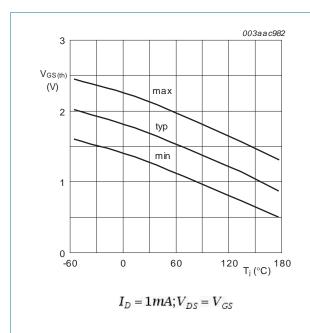


Fig 11. Gate-source threshold voltage as a function of junction temperature

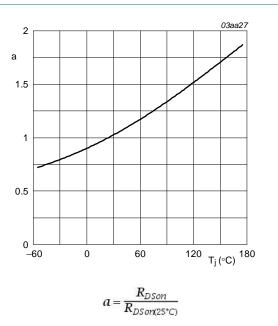


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

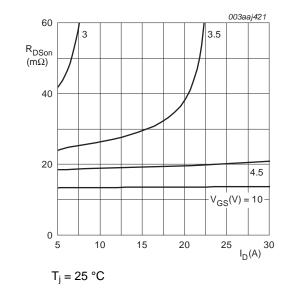


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

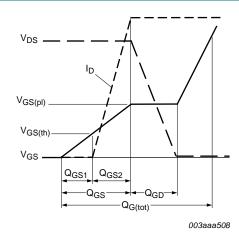


Fig 14. Gate charge waveform definitions

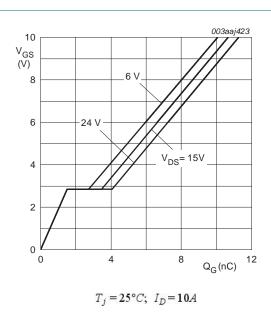
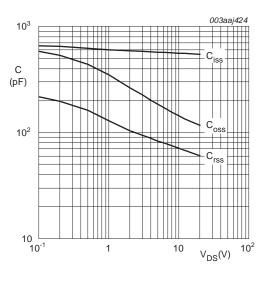
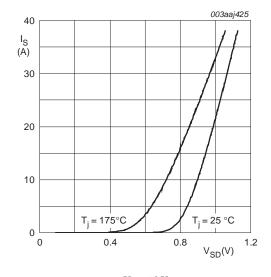


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = \mathbf{0}V; \ f = \mathbf{1}MHz$ 

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = \mathbf{0} V$ 

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 7. Package outline

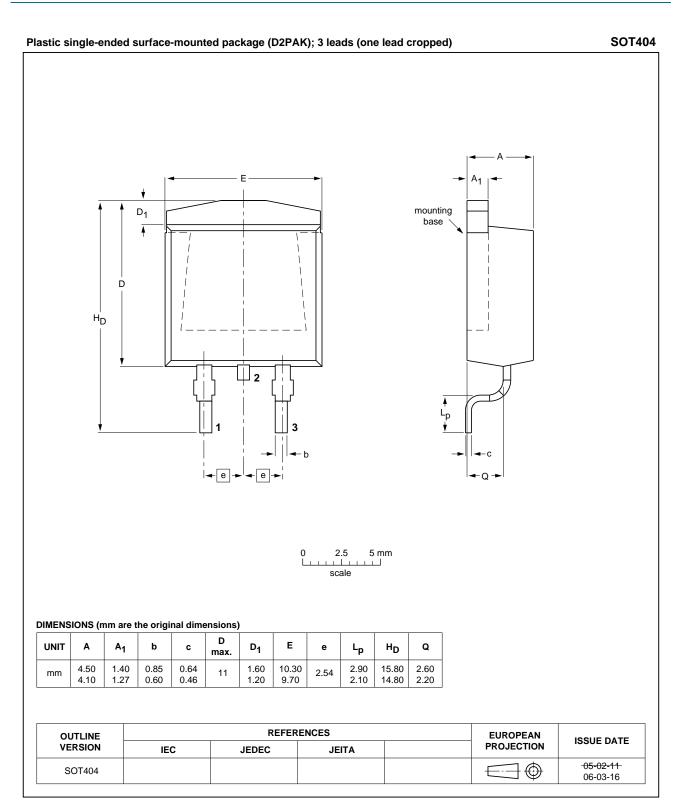


Fig 18. Package outline SOT404 (D2PAK)

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# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-30BL v.2	20120403	Product data sheet	-	PSMN017-30BL v.1
Modifications:	<ul><li>Status changed</li><li>Various change</li></ul>	from objective to product. es to content.		
PSMN017-30BL v.1	20120228	Objective data sheet	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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## **PSMN017-30BL**

#### N-channel 30 V 17 mΩ logic level MOSFET in D2PAK

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# **PSMN017-30BL**

## **Nexperia**

N-channel 30 V 17 m $\Omega$  logic level MOSFET in D2PAK

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For more information, please visit: http://www.nexperia.com
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